

**Amendments to the Specification:**

**Please replace the paragraph beginning at page 3, line 23, with the following amended paragraph:**

Figs. 2A to ~~[[2E]]~~ 2F are cross-sectional diagrams of a substrate to explain an embodiment of a semiconductor manufacturing method of the present invention.

**Please replace the paragraph beginning at page 5, line 10, with the following amended paragraph:**

Referring to Figs. 2A to ~~[[2E]]~~ 2F, description will be given of an embodiment of the semiconductor device manufacturing method. Figs. 1A and 1B will be referred to in the description when necessary. Each figure shown in Figs. 2A to ~~[[2E]]~~ 2F corresponds to a cross section along one-dot-chain line A2-A2 of Fig. 1A.

**Please replace the paragraph beginning at page 8, line 11, with the following amended paragraph:**

As shown in ~~Fig. 2E~~ Fig. 2F, a cobalt silicide film 25 is formed on an upper surface of the wiring 3. Description will now be given of a method of forming the cobalt silicide film 25. ~~[[A]]~~ As shown in Fig. 2E, a 10 nm thick cobalt (Co) film 26 and a 30 nm thick ~~titan~~ titanium nitride (TiN) film 27 are deposited on the overall surface of the silicon substrate 19 by sputtering. In a nitrogen gas atmosphere, thermal treatment is performed for 30 seconds at 500 °C. As a result of reaction between the wiring 3 and the cobalt film, a cobalt silicide film 25 is formed. The cobalt film 26 which did not react with the wiring 3 and the ~~titan~~ titanium nitride film 27 are removed in a wet process using a mixture including sulfuric acid and hydrogen peroxide.